

## 1N60PW-1N60SW

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### Schottky Barrier Diode

#### FEATURES

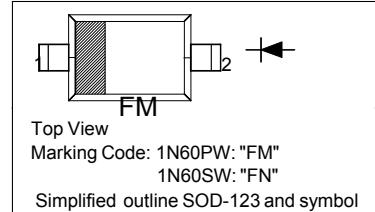
- High reliability
- Low forward voltage and reverse current

#### APPLICATIONS

- For electronic calculator, etc.
- Low current rectification and high speed switching

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



#### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

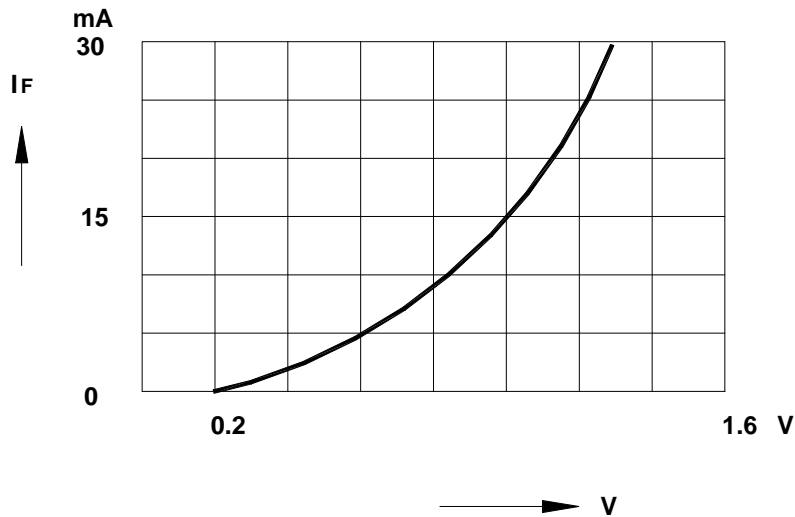
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	45	V
Reverse Voltage	$V_R$	10	V
Peak Forward Current	$I_{FM}$	150	mA
Average Rectified Output Current	$I_O$	50	mA
Surge Forward Current	$I_{surge}$	500	mA
Junction Temperature	$T_J$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{Stg}$	-55 to +125	$^\circ\text{C}$

#### Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ )

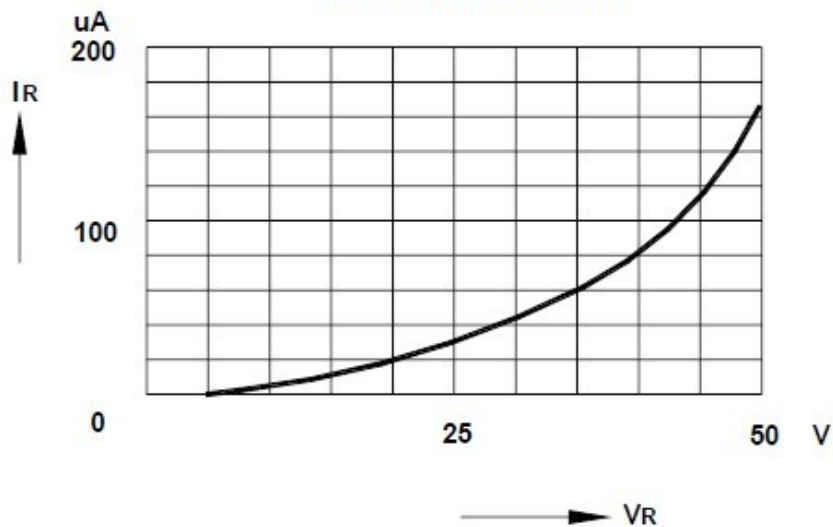
Parameter	Symbol	Min.	Max.	Unit
Forward Current at $V_F = 1\text{ V}$	$I_F$	4	-	mA
Reverse Current at $V_R = 10\text{ V}$	$I_R$	-	50 100	$\mu\text{A}$
Reverse Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_R$	45	-	V
Junction Capacitance at $f = 1\text{ MHz}$ , $V = -1\text{ V}$	$C_J$	-	1	pF
Rectification efficiency at $V_i = 2\text{ Vrms}$ , $R = 5\text{ K}\Omega$ , $C = 20\text{ pF}$ , $f = 40\text{ MHz}$	$\eta$	55	-	%

Pair  $\Delta I \leq 6\text{ mA}$  at 1V,  $\Delta I \leq 20\text{ }\mu\text{A}$  at 10 V

### Forward Characteristics



### Reverse Characteristics





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**SOD-123**



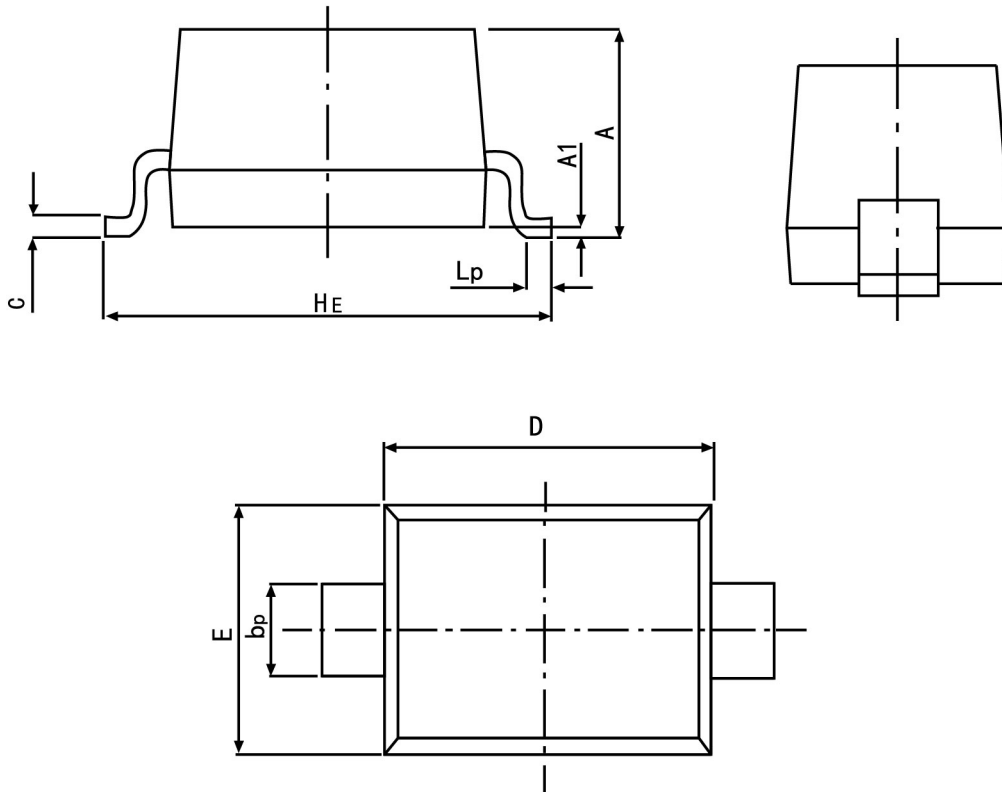
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**PACKAGE OUTLINE**

Plastic surface mounted package; 2 leads

SOD-123



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.20
bp	0.50	0.60
C	0.100	0.135
D	2.55	2.75
E	1.55	1.65
HE	3.55	3.85
A1	0.01	0.10
Lp	0.20	0.50